

## 16<sup>th</sup> International Conference on Particle Induced X-ray Emission

**Unravelling secrets from atoms to planets** 

## **PIXE2019 - Programme and Abstracts**



	Tuesday, March 26, 2019	
Session - Det Chair: M. Ka	ectors, Software and Experimental Systems 2	
9:20-10:00	A. Mantero	1.3
9.20-10.00	PIXE Simulation in Geant4, an Update	
10:00-10:20	V. Bilyk PIXE depth profiling of components in heavy-ion irradiated Zr alloys	0.11
	E. Obiajunwa	0.12
10:20-10:40	Ion beam analysis facility at the centre for energy research & development at	
	Ile-Ife Nigeria and its application in research	
10:40-11:00	K. Phelan CryoGenX - A High-resolution Spectrometer for Advanced Nuclide Analysis	0.13
	Coffee/Tea break	
Session - Sim	ulation and Techniques Combination 1	
Chair: T. Call		
11:20-11:40	M. Bailey	0.14
	Ion Beam Analysis for the 2020's : An Integration of Elemental Mapping and Omics	0.15
11:40-12:00	D. Strivay Analysis of archeological artefacts from Ostia and Arena Roman sites by PIXE-PIGE	0.15
	and Proton Activation Analysis	
12:00-12:20	V. Corregidor	0.16
	PIXE and RBS on CIGS solar cells to study the elemental distribution	
12:20-14:00	Lunch	
Socian Sim	nulation and Techniques Combination 2	
Chair: J. F. D.		
	C. Ryan	I.2
14:00-14:40	PIXE and synchrotron XRF imaging: Comparisons using the Maia detector array	
14:40-15:00	J. Cruz	0.17
	μ-PIXE/μ-EBS and SEM analysis of surface spots in gold coins/discs	
	from the Portuguese Mint House  Z. Kertész	0.18
15:00-15:20	What killed the apothecarius of Vác in 1763? Micro-PIXE study of mummified bones	0.10
	Coffee/Tea break	
	tural Heritage & Geological Applications 1	
Chair: Ž. Šmi		0.40
15:40-16:00	Z. Szőkefalvi-Nagy Ancient glass analysis by milli-PIXE and PGAA - the case of late Roman	0.19
	and Byzantine glasses	
16:00-16:20	F. Munnick	0.20
	Characterization of Goethe's prisms by external ion beam	
16:20-16:40	H. Hofsäss	0.21
10.20 10.10	PIXE analysis of antique pottery from the Mediterranean sea area	
16:40-17:40	Round Table on Detectors & Software C. Jeynes	
	C. Jeynes	
	Poster Session 2	
17:40-19:00		
17:40-19:00		
	IAC - IHC	
17:40-19:00 19:00-20:00	IAC - IHC Meeting	
	Meeting	
19:00-20:00	Wednesday, March 27, 2019 Buses to ESTM	
19:00-20:00 9:00-10:00	Wednesday, March 27, 2019 Buses to ESTM	
19:00-20:00 9:00-10:00 <b>Open Session</b> Chair: M. A.	Meeting  Wednesday, March 27, 2019  Buses to ESTM  Reis  J. L. Campbell	1.5
19:00-20:00 9:00-10:00 <b>Open Session</b>	Meeting  Wednesday, March 27, 2019  Buses to ESTM  Reis	1.5

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24-29 March $2019\cdot$  Cultural and Congress Centre of Caldas da Rainha

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# PIXE and RBS on CIGS solar cells to study the elemental distribution

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0.16

#### Abstract

Among thin film solar cells materials CIGS materials (CuIn1-xGaxSe2) are the most used, jointly with CdTe, having the advantages of their application in flexible substrates, long term stability, high electrical performance and production versatility. Although they are available in the photovoltaic market, at the same time a lot of research is on-going in order to increase the cell photo conversion efficiency (about 23 % at the moment) not only in lab conditions, but also under real conditions. Active optoelectronic defects, as composition inhomogeneities, created during the manufacturing process, are the main responsible for efficiency limitations. For instance, even small changes in the In-Ga depth distribution inside the CIGS layer will influence the bandgap and thus, the light to power conversion efficiency of the solar cell. RBS and PIXE techniques coupled to a nuclear microprobe can reliably accomplish both the determination of the elemental surface distribution and their depth distribution even in the final electronic device. Three different solar cell devices (two of them belonging to the same substrate) were irradiated with 900 keV proton beam and the NDF software code was used to perform the Total-IBA approach through the simultaneous and self-consistent analysis of the data collected from PIXE and RBS spectra. Results will be presented and discussed.